

2SK2736

Silicon N Channel DV-L MOS FET
High Speed Power Switching

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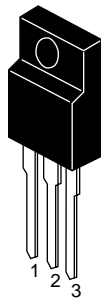
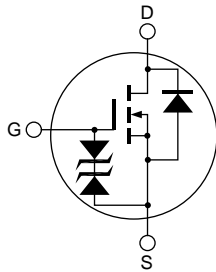
ADE-208-544
1st. Edition

Features

- Low on-resistance
 $R_{DS(on)} = 20 \text{ m}\Omega$ typ. ($V_{GS} = 10\text{V}$, $I_D = 15 \text{ A}$)
- 4V gate drive devices.
- High speed switching

Outline

TO-220CFM



1. Gate
2. Drain
3. Source

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	30	A
Drain peak current	$I_{D(pulse)}^{*1}$	120	A
Body to drain diode reverse drain current	I_{DR}	30	A
Channel dissipation	Pch^{*2}	25	W
Channel temperature	Tch	150	$^\circ\text{C}$
Storage temperature	$Tstg$	-55 to +150	$^\circ\text{C}$

Notes: 1. $PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$

2. Value at $T_c = 25^\circ\text{C}$

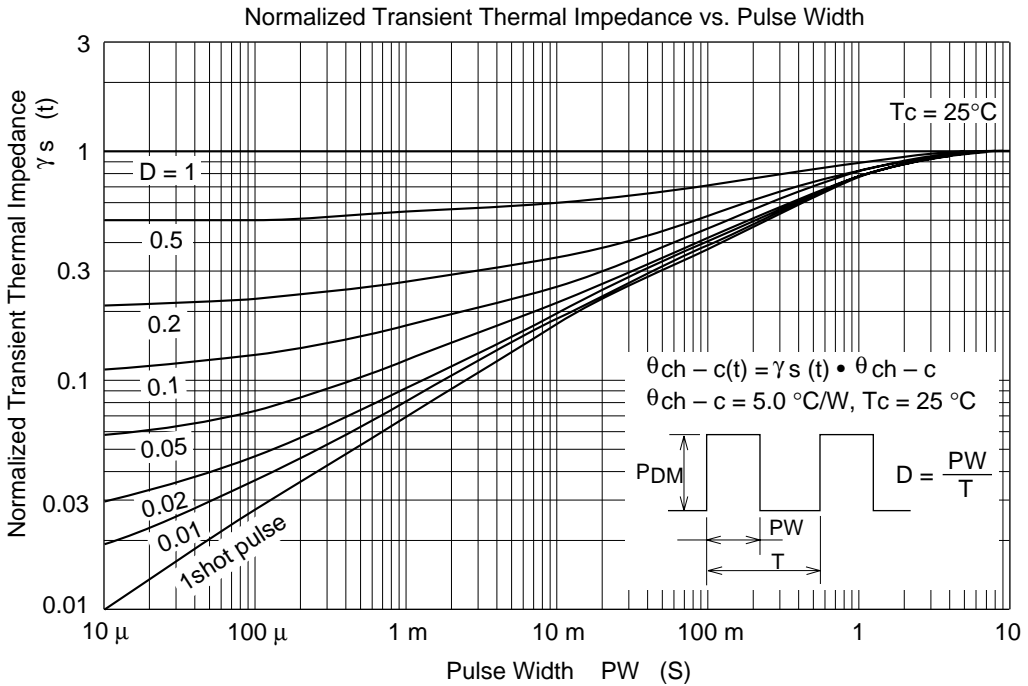
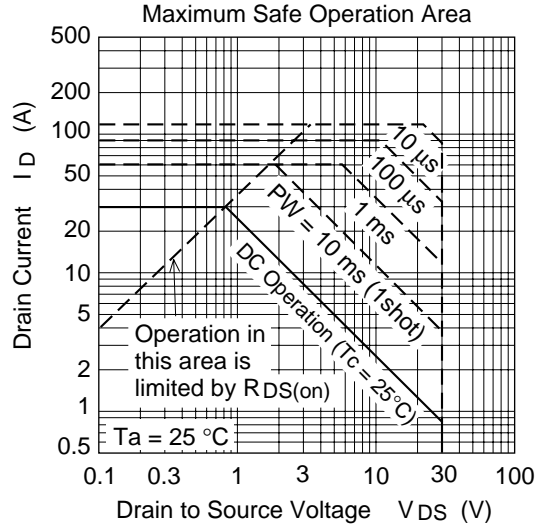
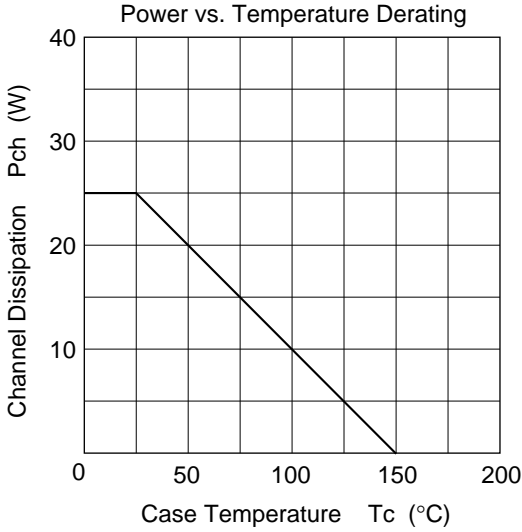
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10\text{mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100\mu\text{A}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 30\text{V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16\text{V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	20	28	$\text{m}\Omega$	$I_D = 15\text{A}$, $V_{GS} = 10\text{V}^{*1}$
	$R_{DS(on)}$	—	35	50	$\text{m}\Omega$	$I_D = 15\text{A}$, $V_{GS} = 4\text{V}^{*1}$
Forward transfer admittance	$ y_{fs} $	12	18	—	S	$I_D = 15\text{A}$, $V_{DS} = 10\text{V}^{*1}$
Input capacitance	C_{iss}	—	750	—	pF	$V_{DS} = 10\text{V}$
Output capacitance	C_{oss}	—	520	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	210	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	16	—	ns	$V_{GS} = 10\text{V}$, $I_D = 15\text{A}$
Rise time	t_r	—	260	—	ns	$R_L = 0.67\Omega$
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	
Fall time	t_f	—	90	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 30\text{A}$, $V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	45	—	ns	$I_F = 30\text{A}$, $V_{GS} = 0$ $di_F/dt = 50\text{A}/\mu\text{s}$

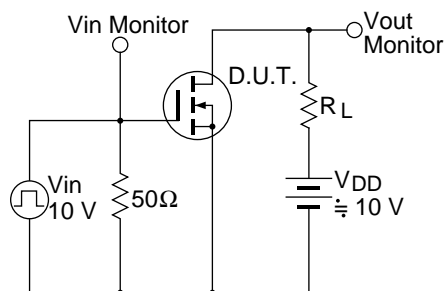
Note: 1. Pulse test

See characteristics curves of 2SK2684

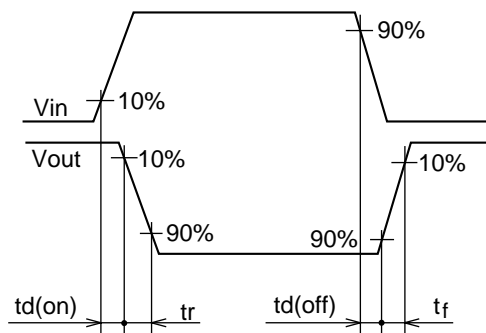
Main Characteristics



Switching Time Test Circuit

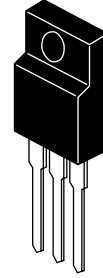
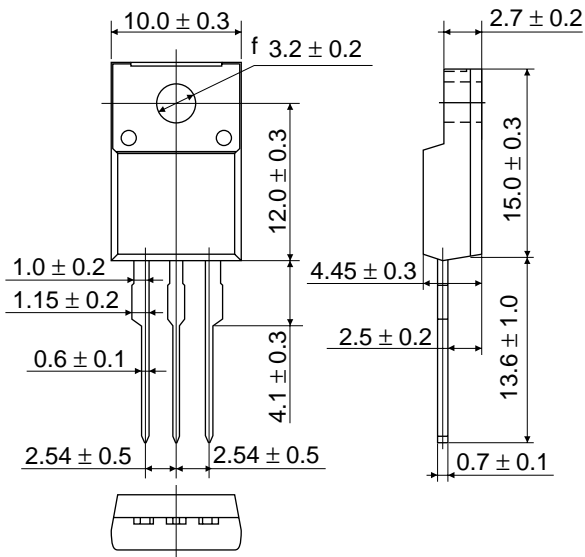


Waveform



Package Dimensions

Unit: mm



Hitachi Code	TO-220CFM
EIAJ	—
JEDEC	—

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL North America : <http://semiconductor.hitachi.com/>
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building, No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

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